

00583530-060100

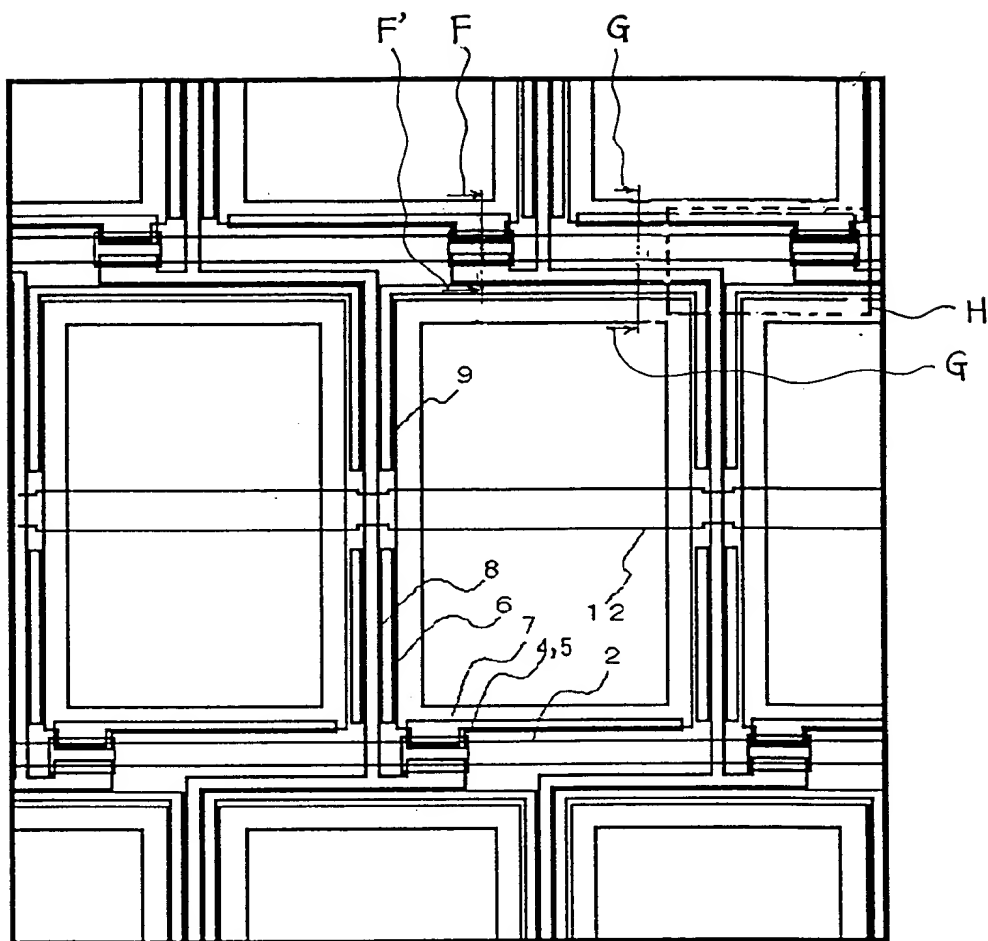


Fig. 1
PRIOR ART

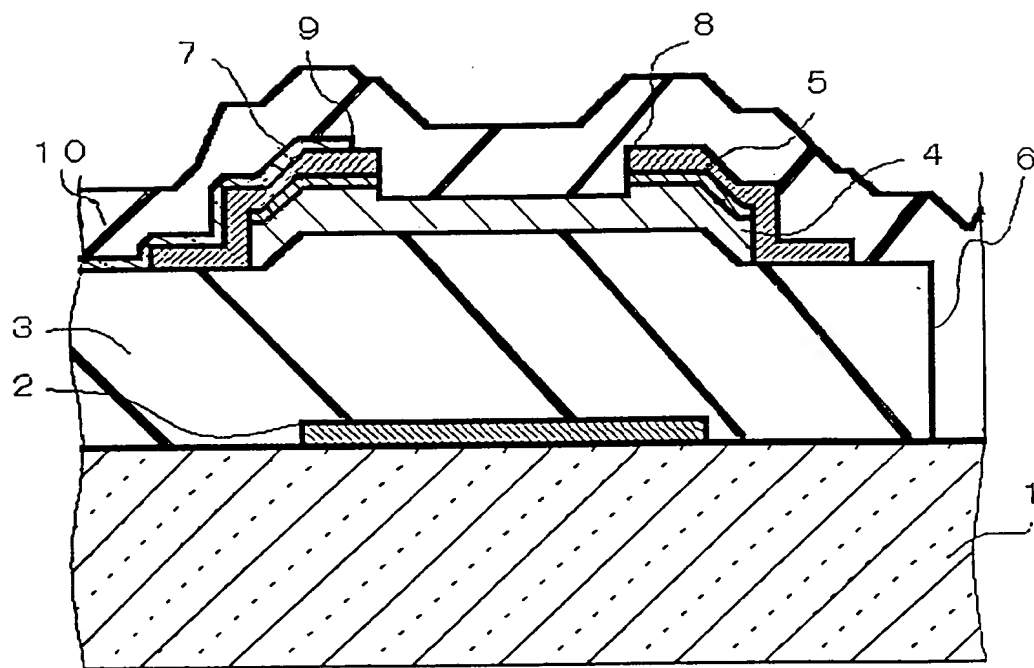


Fig. 2
PRIOR ART

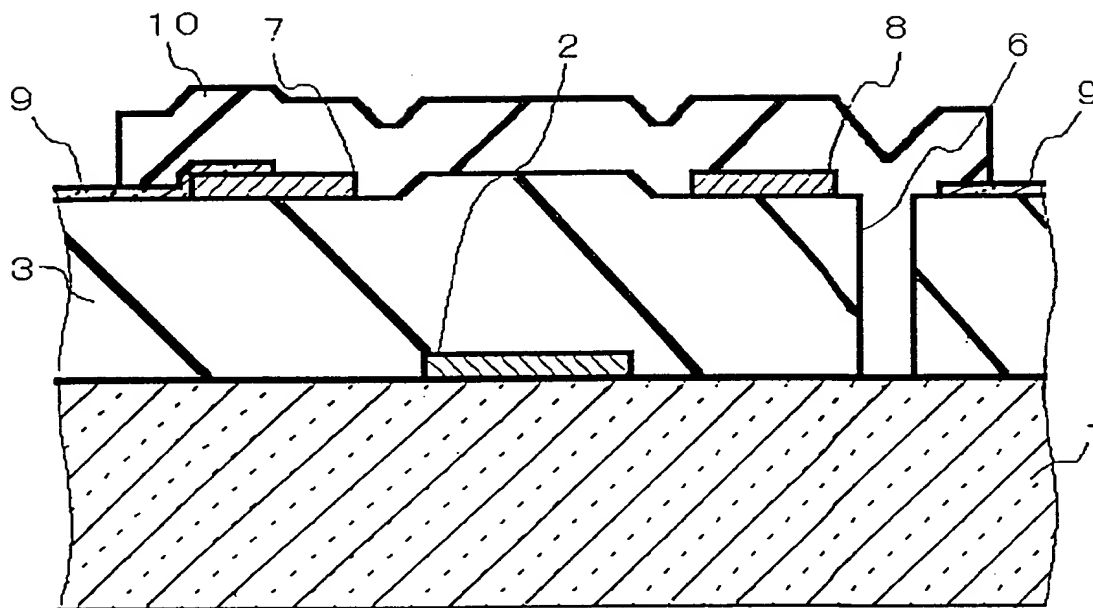


Fig. 3
PRIOR ART

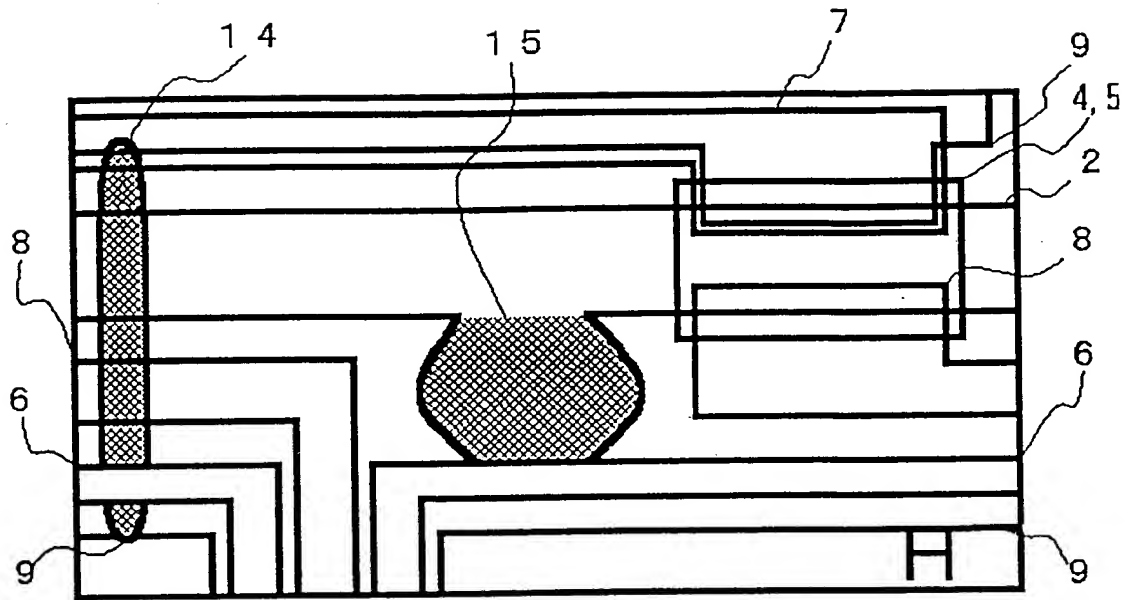


Fig. 5
PRIOR ART

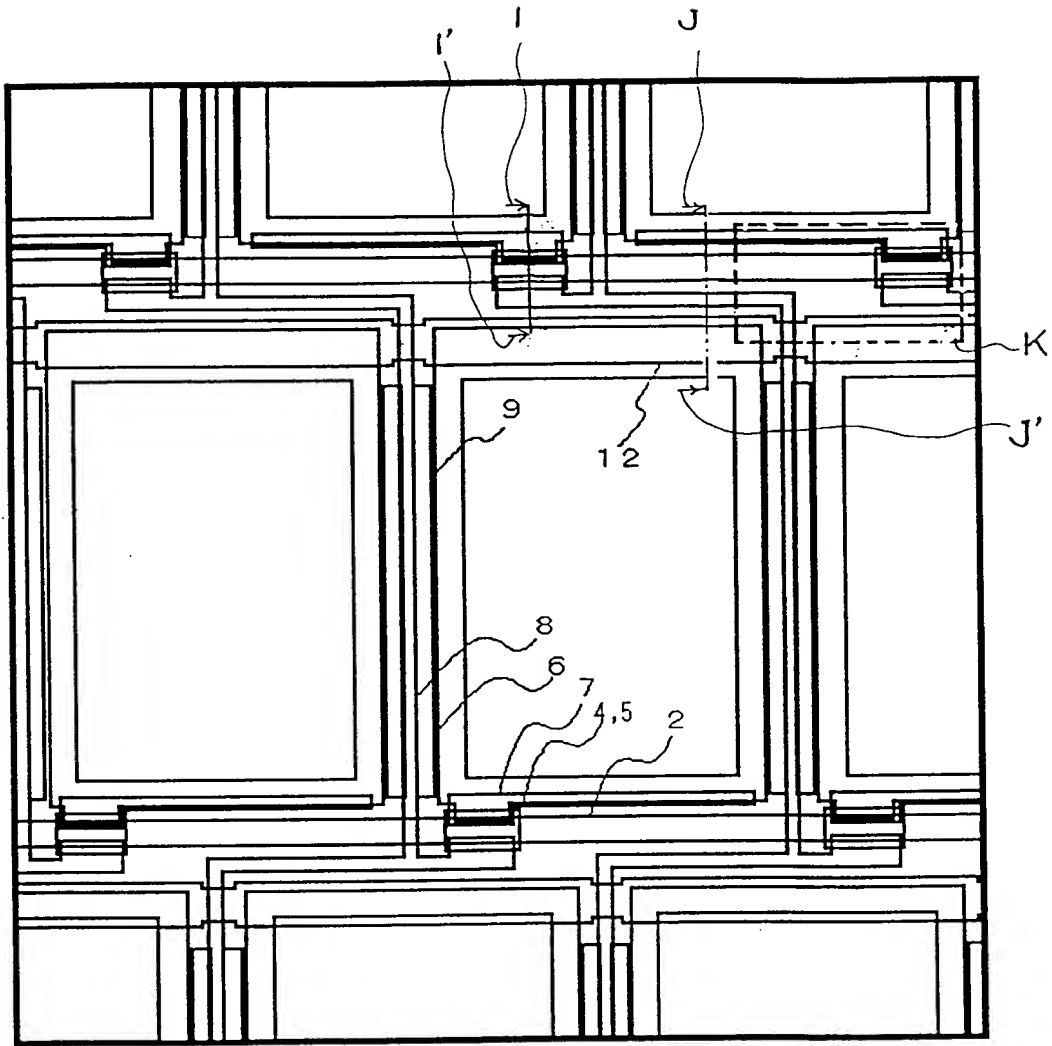


Fig. 6
PRIOR ART

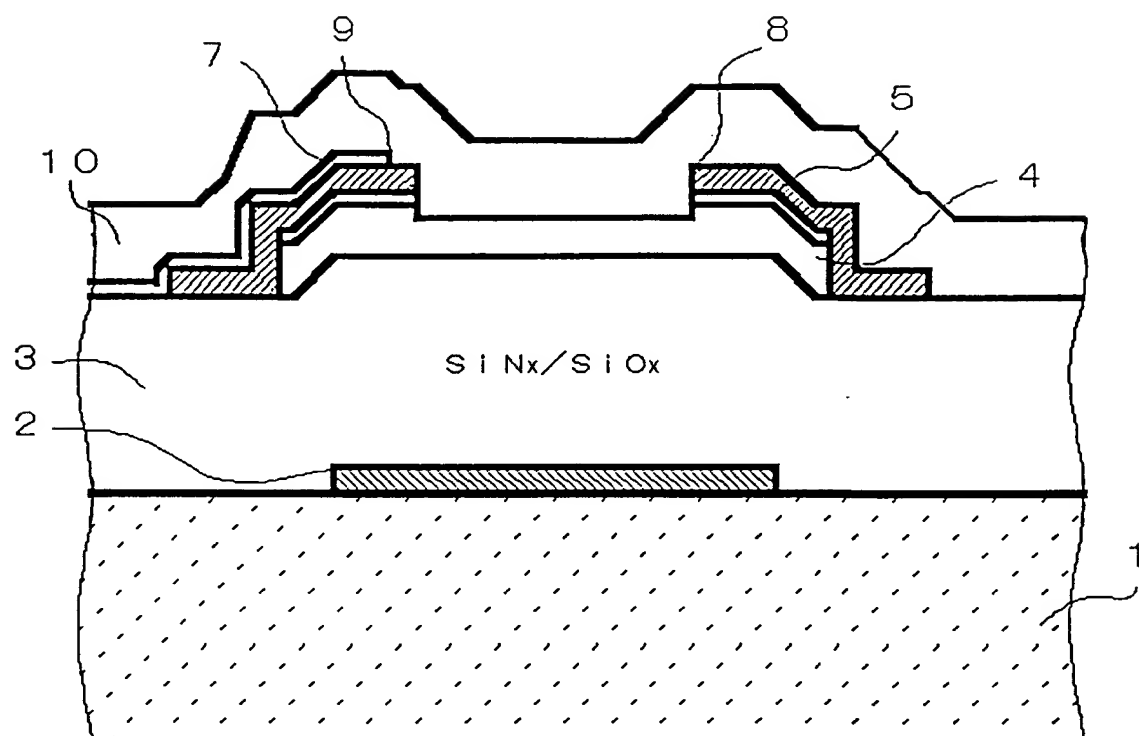


Fig. 7
PRIOR ART

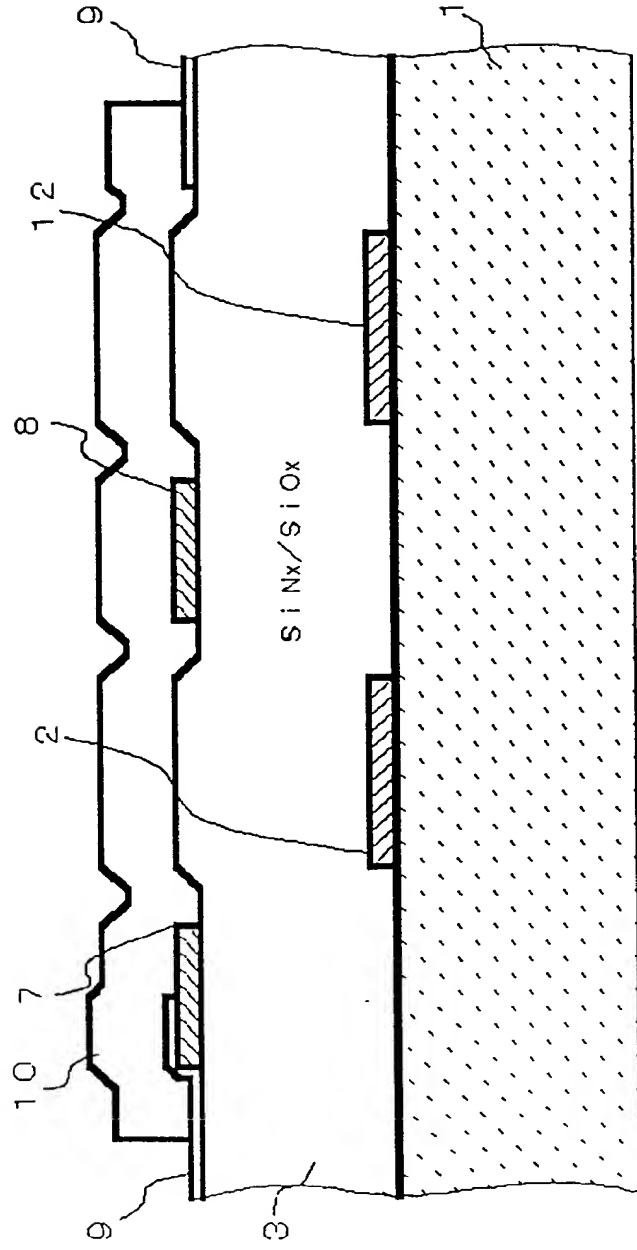


Fig. 8
PRIOR ART

Fig. 9
PRIOR ART

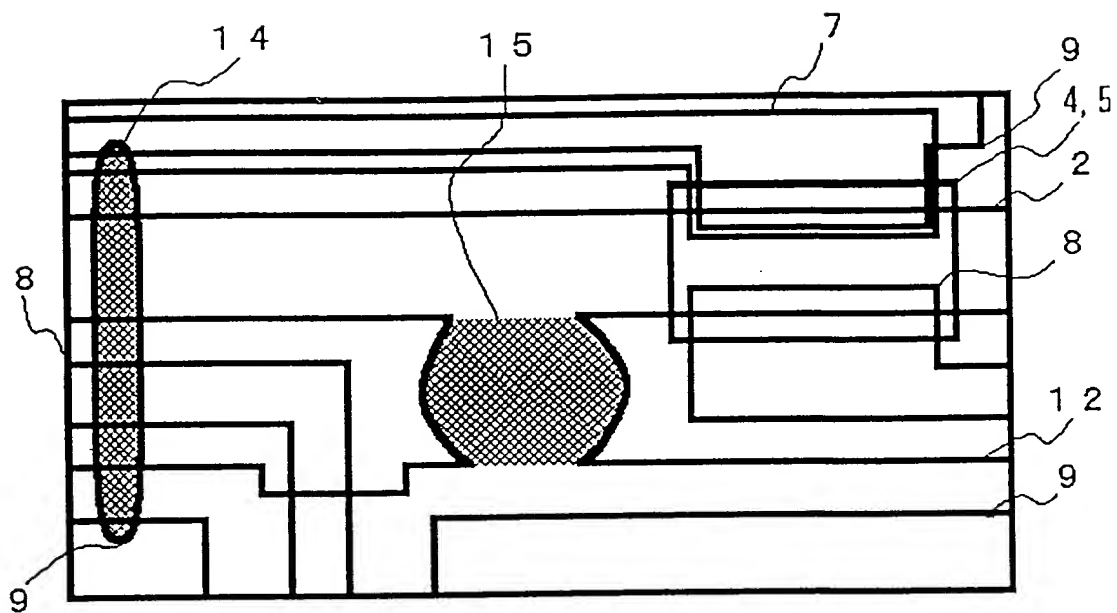


Fig. 10
PRIOR ART

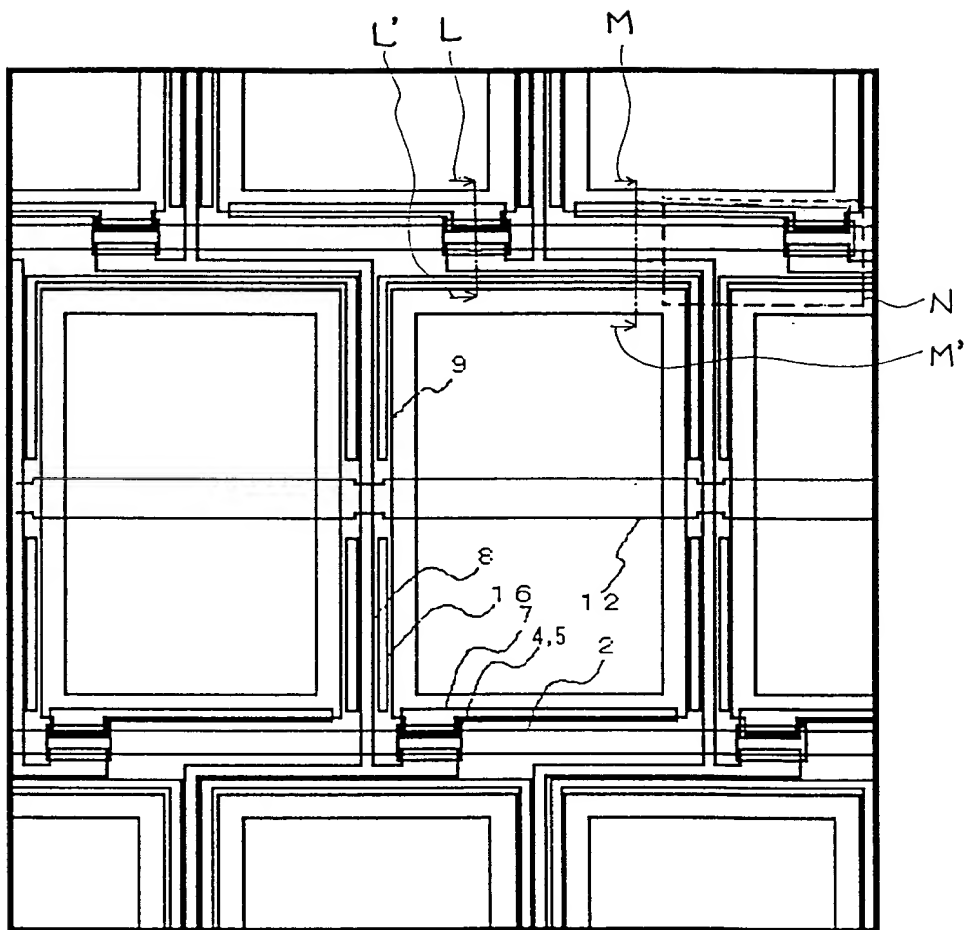


Fig. 11
PRIOR ART

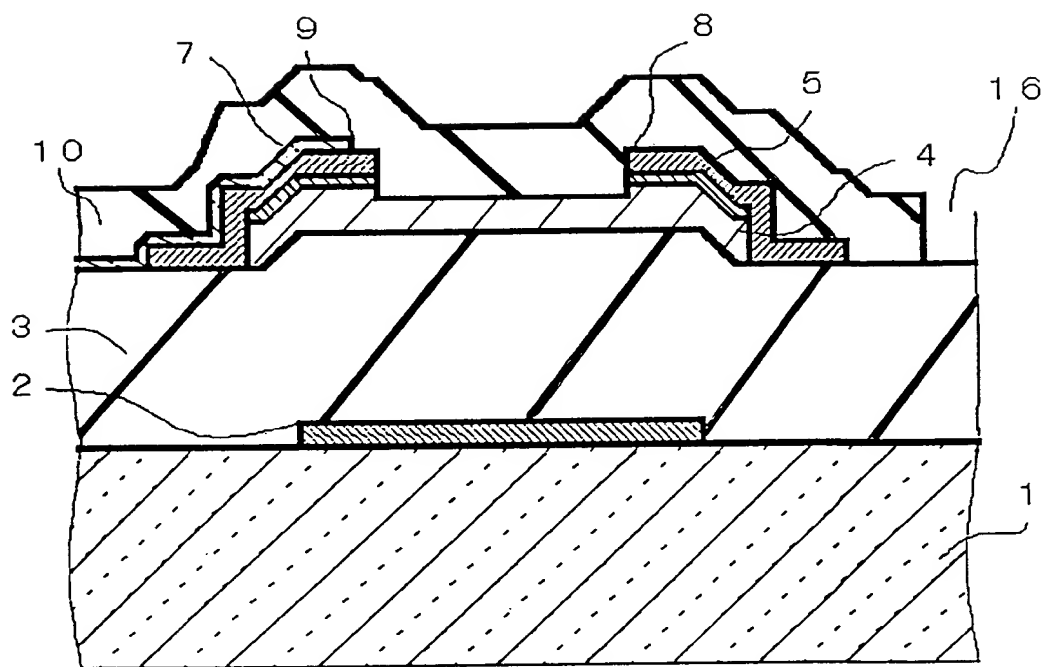


Fig. 12
PRIOR ART

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This cross-sectional view shows a semiconductor device with a repeating pattern of gates and contacts. The device is built on a substrate 1, which is covered by a layer 3. A series of gates 2 are formed on top of layer 3, with a gate dielectric 6 on top of each gate. The gates are separated by spacers 7. Contacts 8 are formed in the spaces between the gates, and a layer 10 is deposited on top of the contacts. A layer 9 is formed on the top surface of the device, and a layer 16 is formed on the top surface of the contacts. A layer 1 is also shown on the bottom surface of the device.

Fig. 13
PRIOR ART

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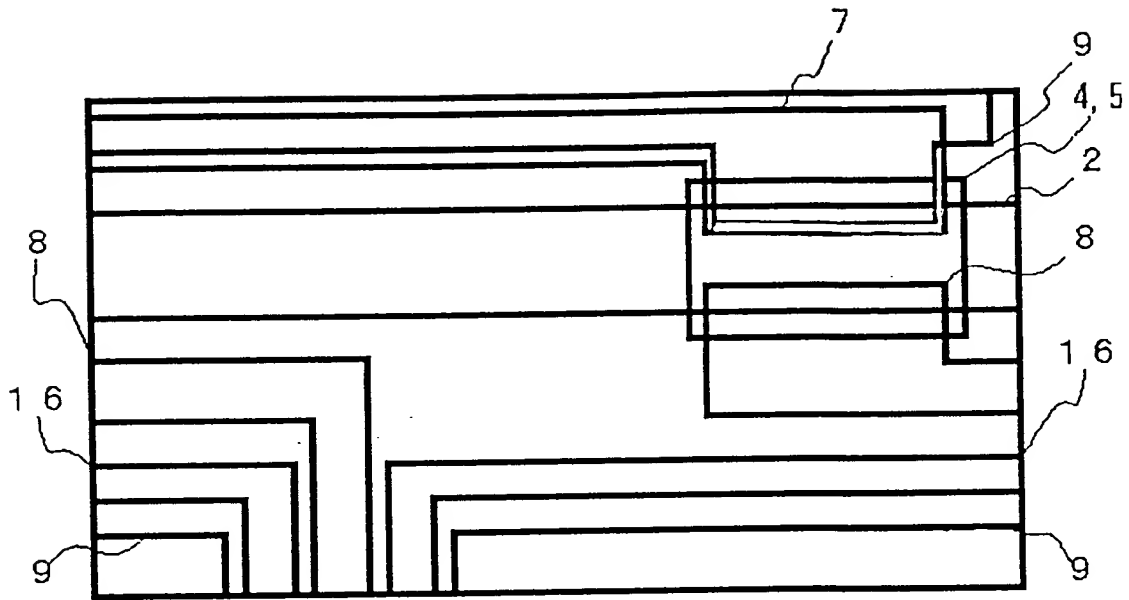


Fig. 14
PRIOR ART

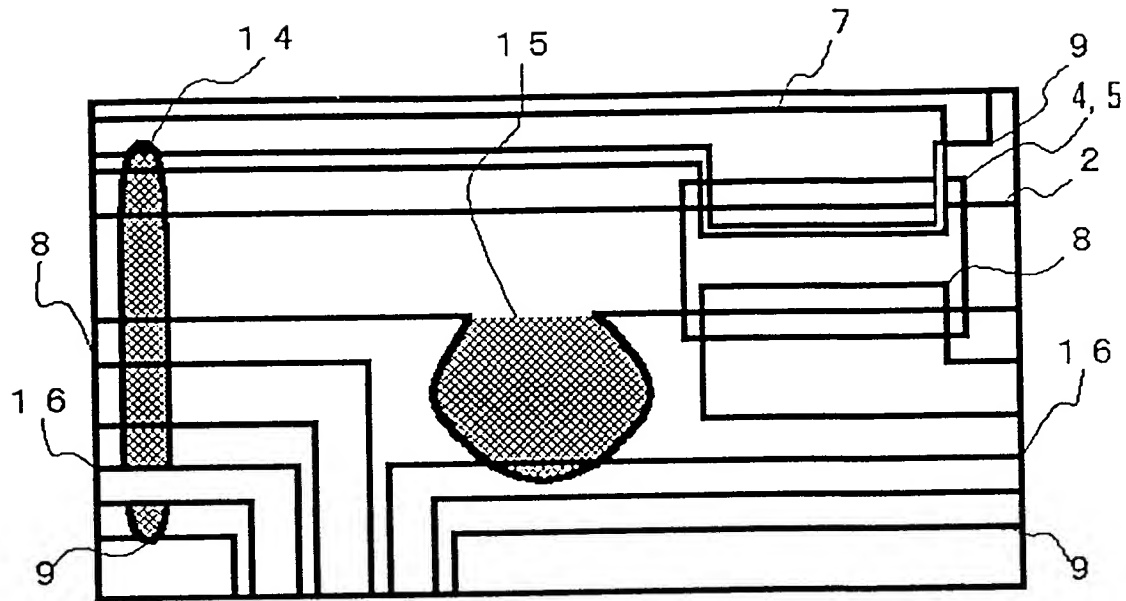


Fig. 15
PRIOR ART

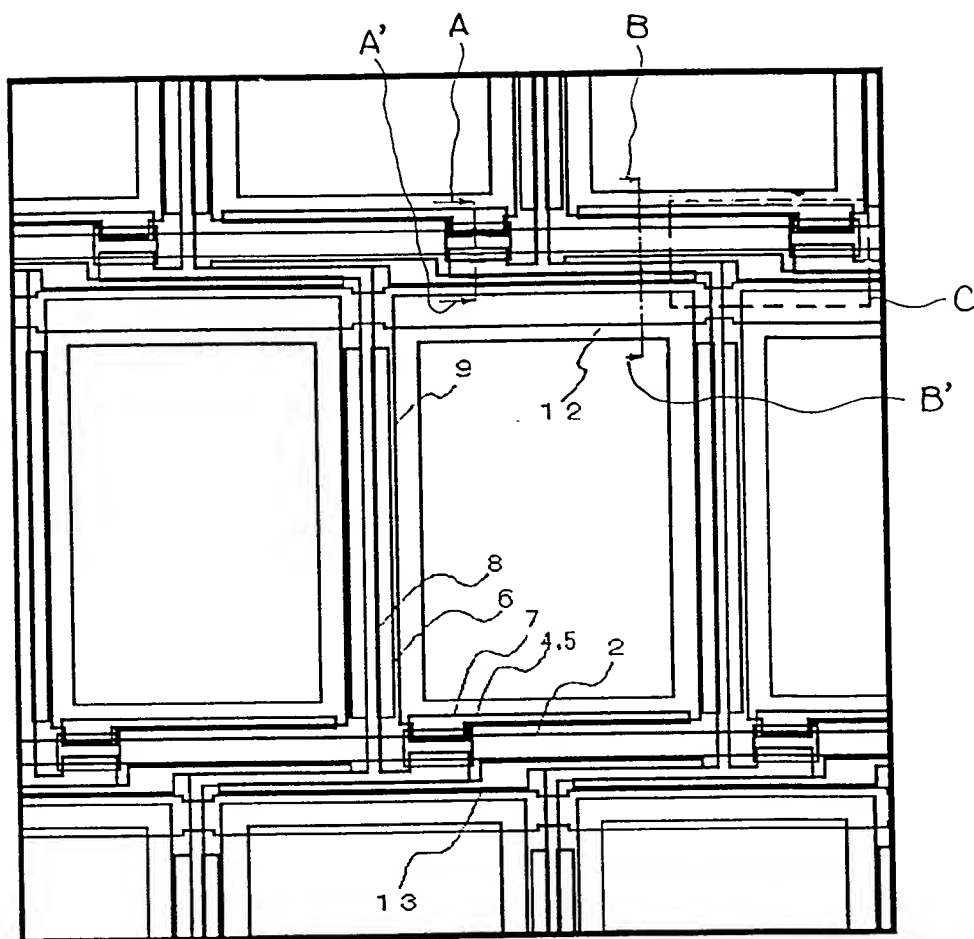


Fig. 16

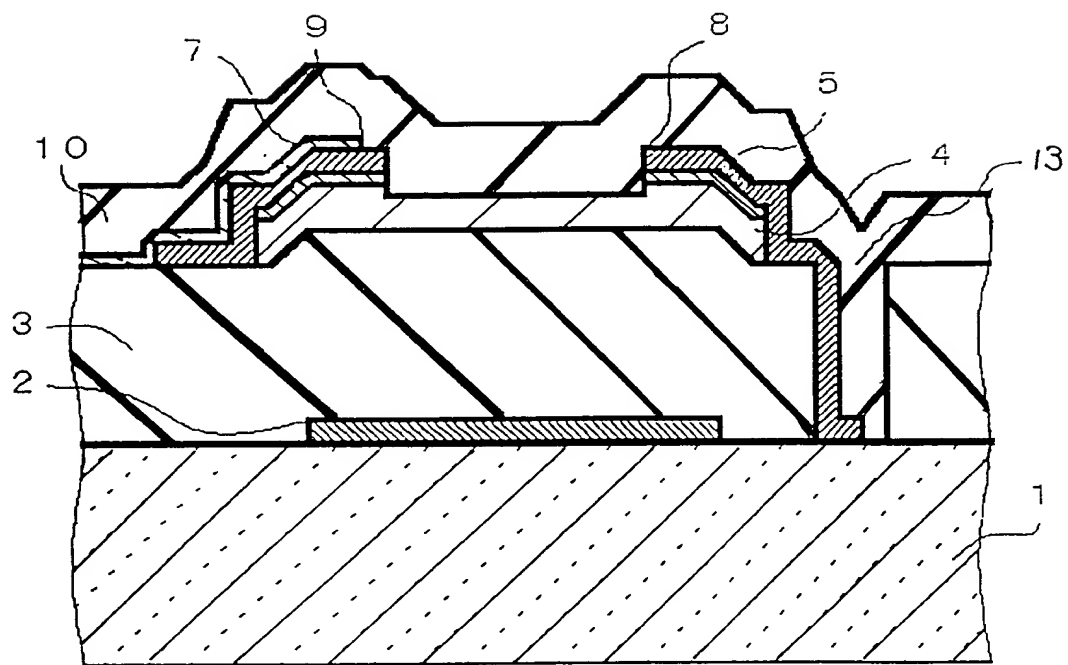


Fig. 17

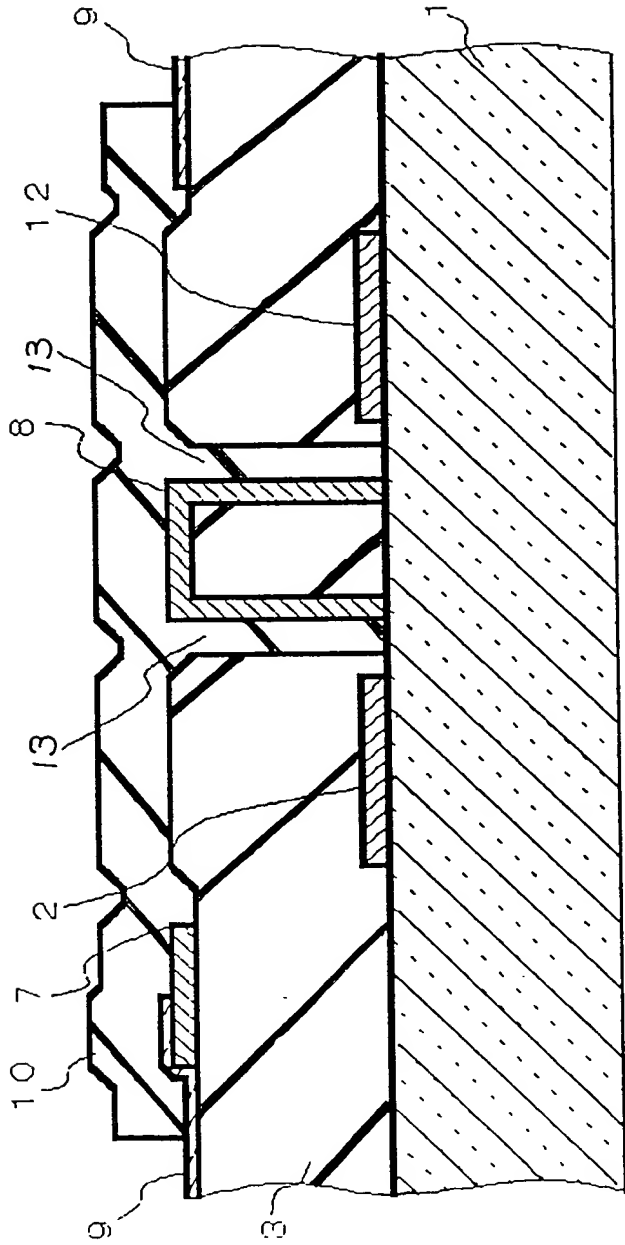


Fig. 18

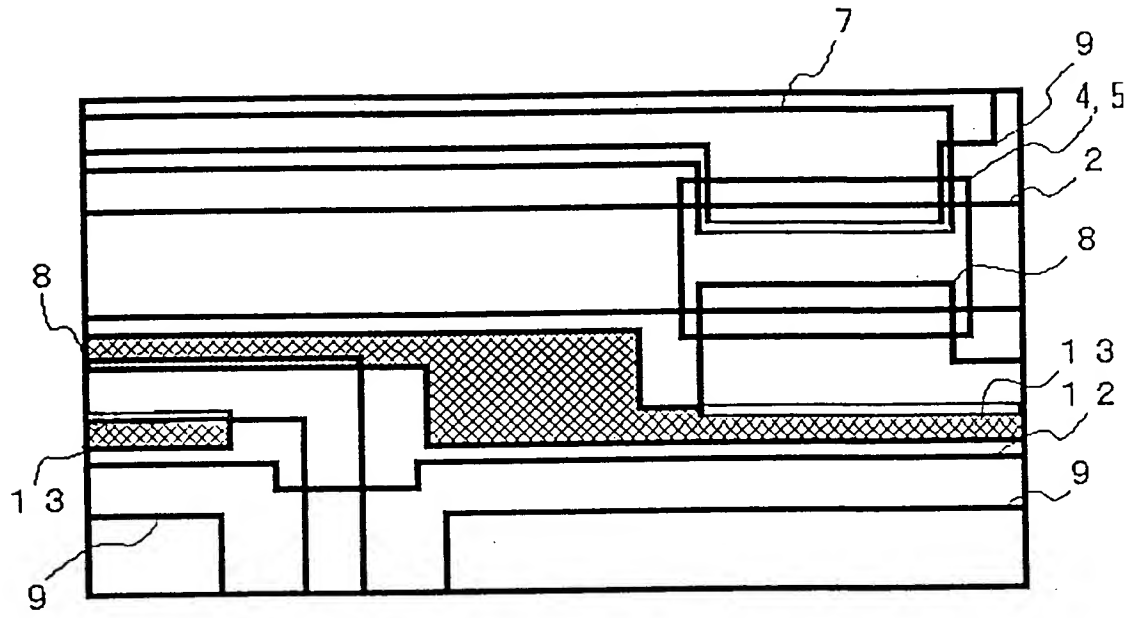


Fig. 19

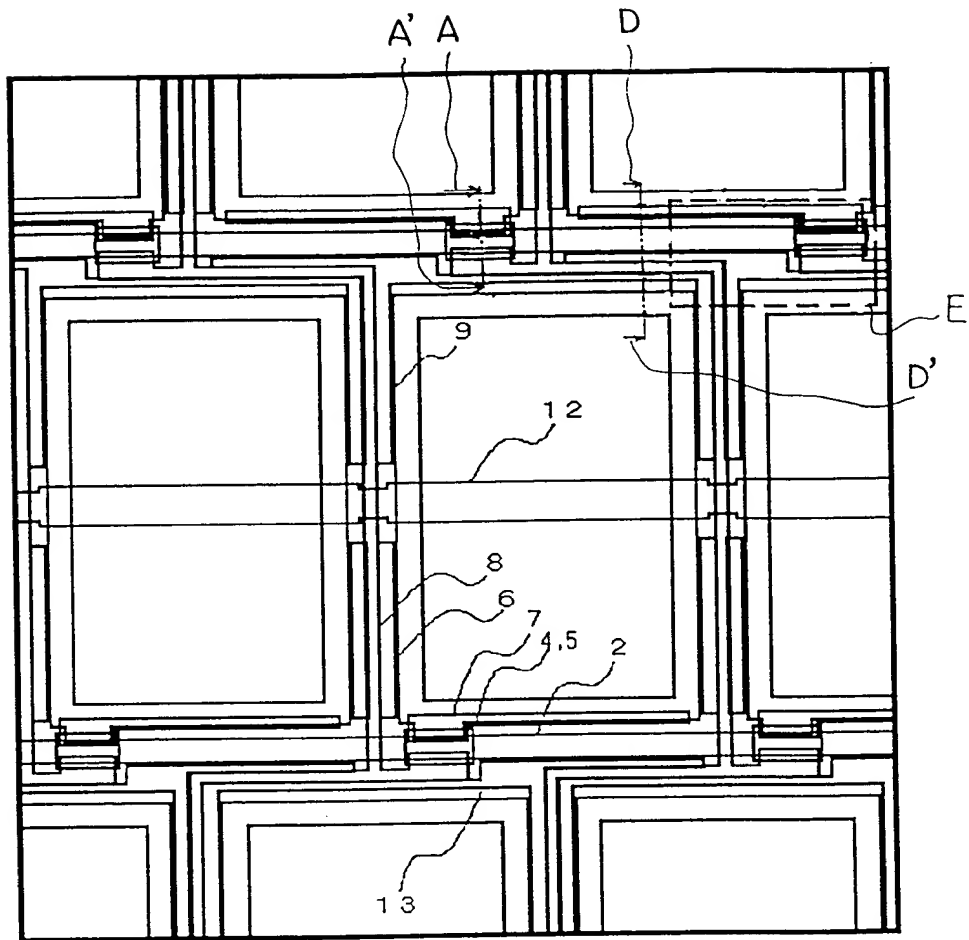


Fig. 21

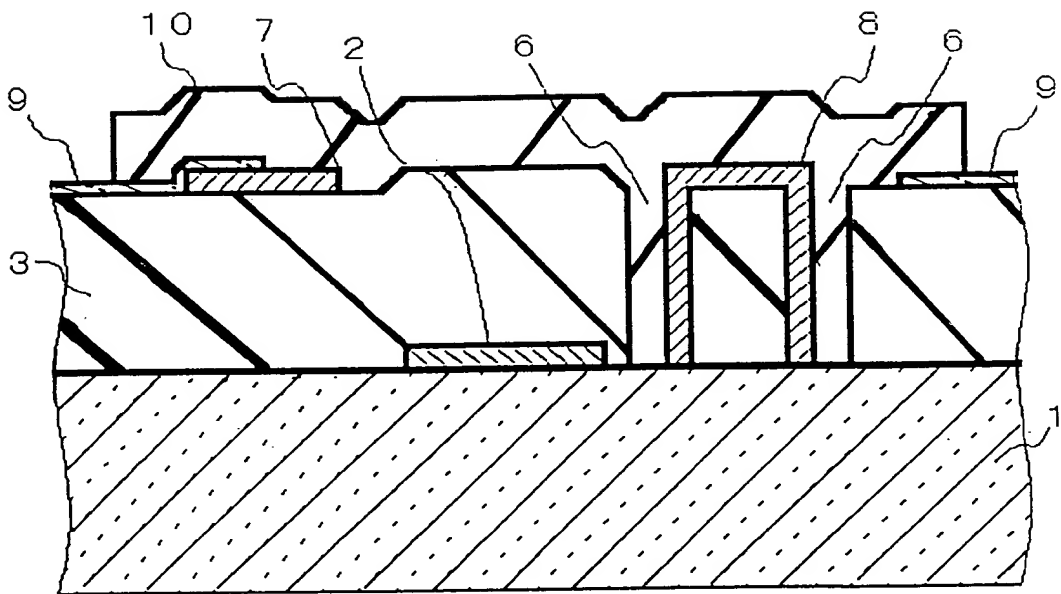


Fig. 22

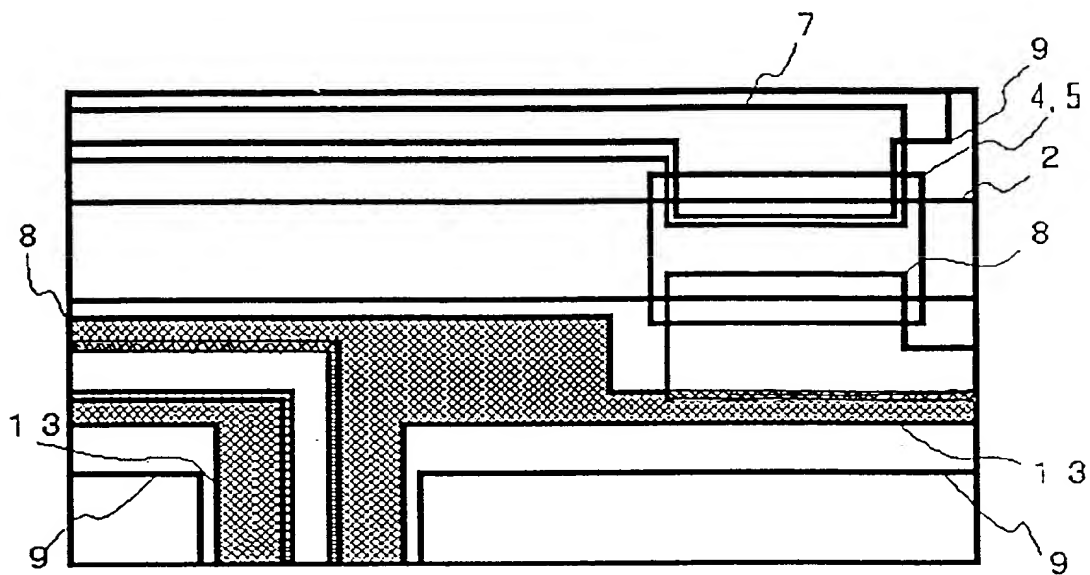


Fig. 23